



April 2000

QFET™

FQAF70N15

N-Channel Power MOSFET

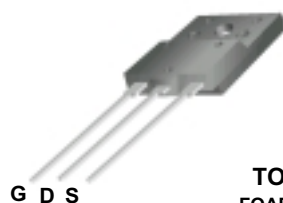
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

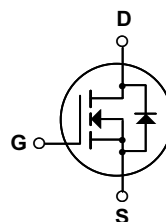
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifier, high efficiency switching for DC/DC converters, and DC motor control, uninterrupted power supply.

Features

- 44A, 150 V, $R_{DS(on)} = 0.028 \Omega$ @ $V_{GS} = 10$ V
- Low gate charge (typical 135 nC)
- Low C_{rss} (typical 135 nC)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



TO-3PF
FQAF Series



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQAF70N15	Units
V_{DSS}	Drain-Source Voltage	150	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	44	A
	- Continuous ($T_C = 100^\circ\text{C}$)	31	A
I_{DM}	Drain Current - Pulsed (Note 1)	176	A
V_{GSS}	Gate-Source Voltage	± 25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	1000	mJ
I_{AR}	Avalanche Current (Note 1)	44	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	13	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	130	W
	- Derate above 25°C	0.86	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.16	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.15	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 120\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 22\text{ A}$	--	0.023	0.028	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 22\text{ A}$ (Note 4)	--	40	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	4150	5400	pF
C_{oss}	Output Capacitance		--	840	1100	pF
C_{rss}	Reverse Transfer Capacitance		--	135	175	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\text{ V}, I_D = 70\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	60	130	ns
t_r	Turn-On Rise Time		--	420	850	ns
$t_{d(off)}$	Turn-Off Delay Time		--	340	690	ns
t_f	Turn-Off Fall Time		--	290	590	ns
Q_g	Total Gate Charge	$V_{DS} = 120\text{ V}, I_D = 70\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	135	175	nC
Q_{gs}	Gate-Source Charge		--	25	--	nC
Q_{gd}	Gate-Drain Charge		--	65	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	44	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	176	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 44 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 70 A, dI _F / dt = 100 A/μs (Note 4)	--	150	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.67	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 0.86\text{ mH}, I_{AS} = 44\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 70\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} = BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

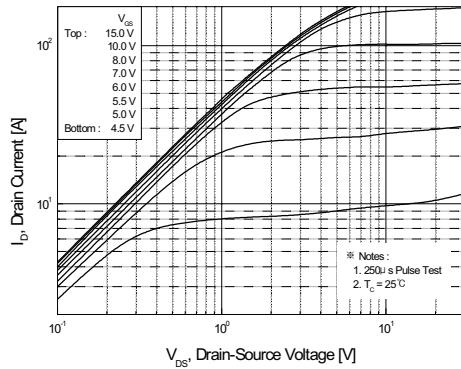


Figure 1. On-Region Characteristics

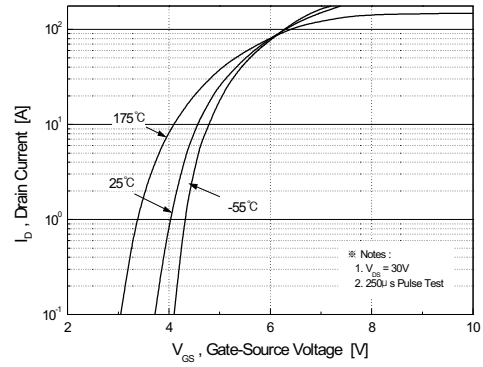


Figure 2. Transfer Characteristics

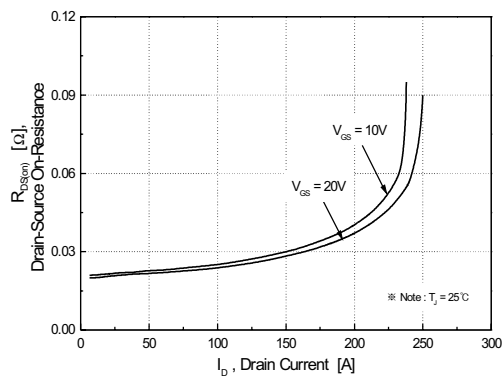


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

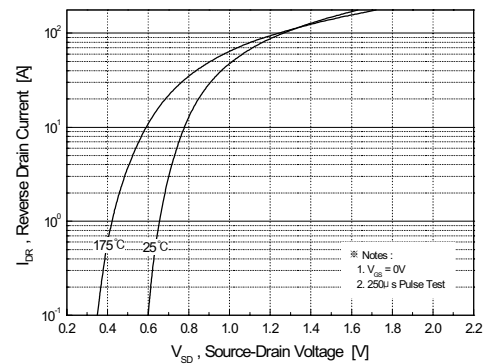


Figure 4. Body Diode Forward Voltage Variation vs. Source Current

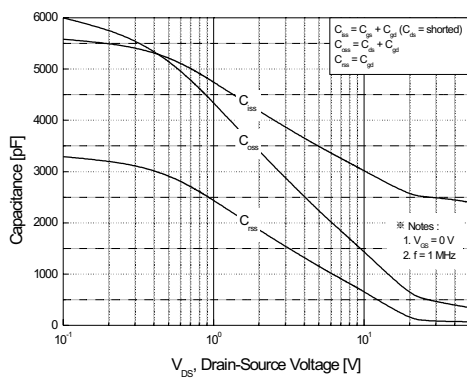


Figure 5. Capacitance Characteristics

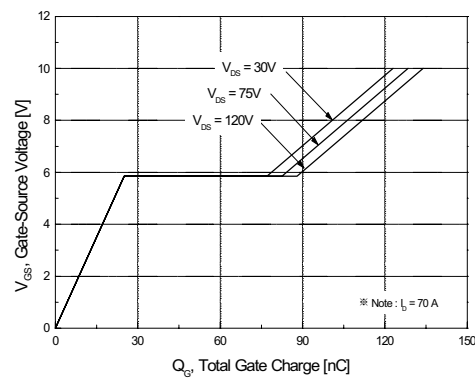


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

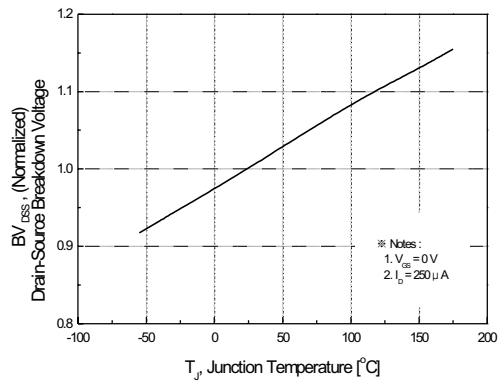


Figure 7. Breakdown Voltage Variation vs. Temperature

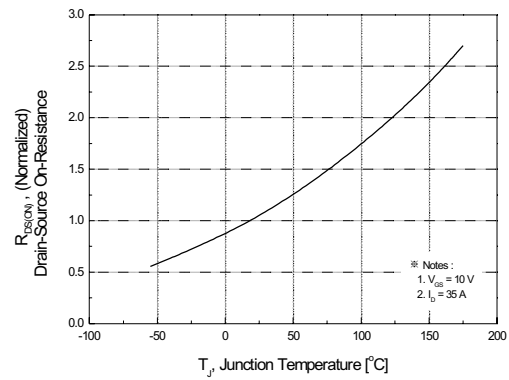


Figure 8. On-Resistance Variation vs. Temperature

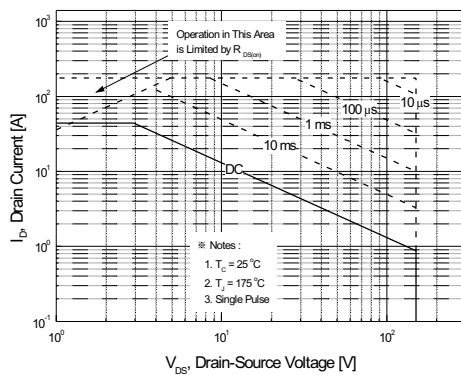


Figure 9. Maximum Safe Operating Area

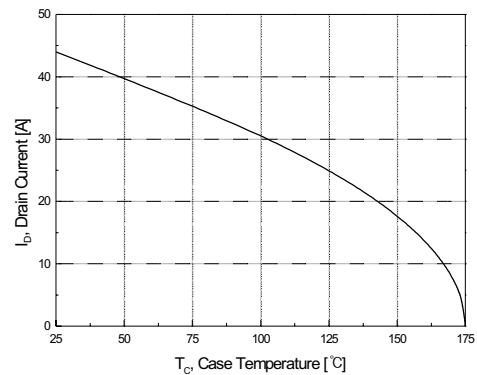


Figure 10. Maximum Drain Current vs. Case Temperature

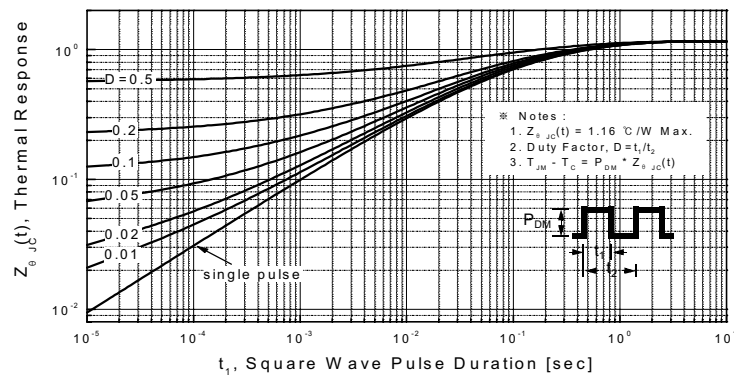
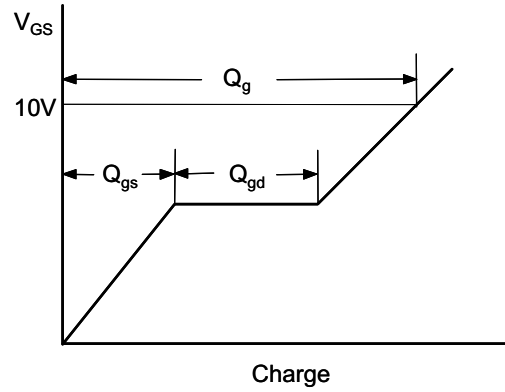
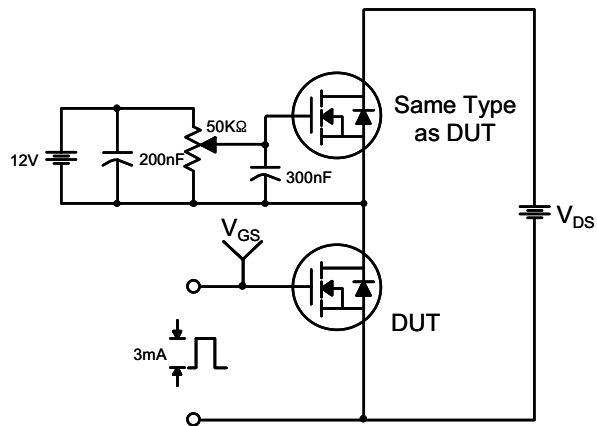
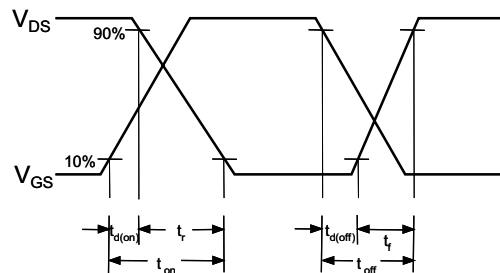
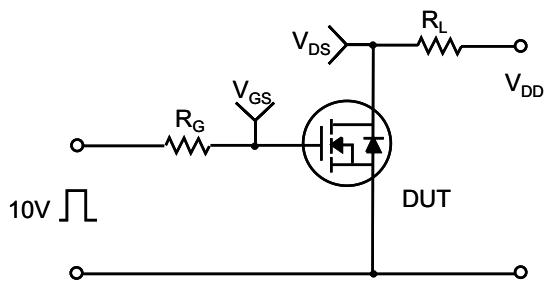


Figure 11. Transient Thermal Response Curve

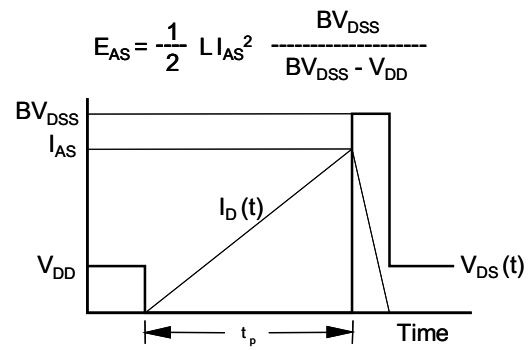
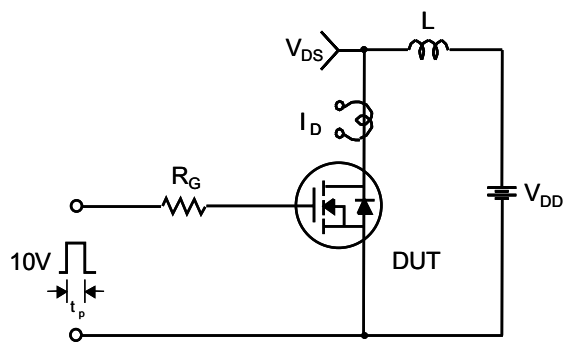
Gate Charge Test Circuit & Waveform



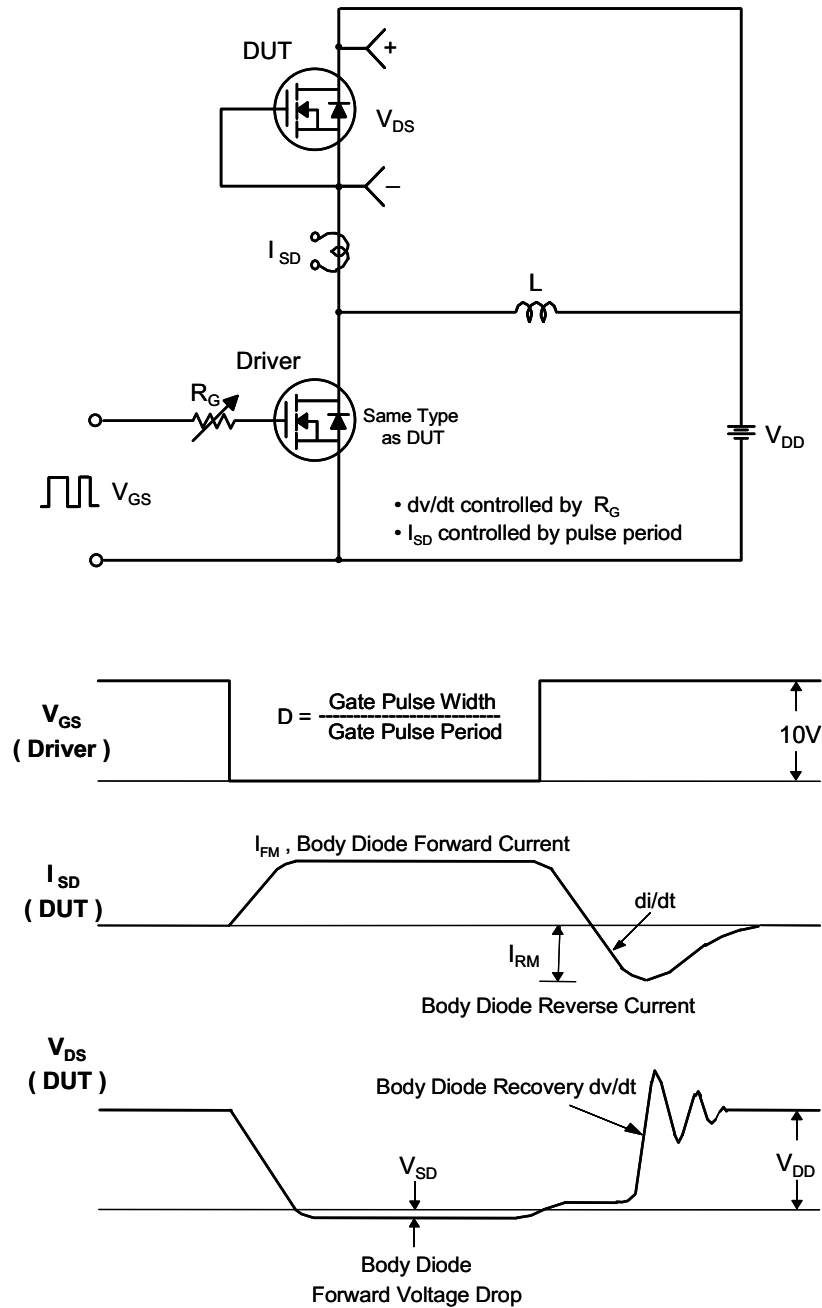
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



Technical drawing of a mechanical part, showing three views: front, side, and top. The drawing includes dimensions and tolerances.

Front View Dimensions:

- Overall width: 15.50 ± 0.20
- Overall height: 26.50 ± 0.20
- Top section height: 4.50 ± 0.20
- Central slot width: 2.00 ± 0.20
- Pin diameter: $\varnothing 3.60 \pm 0.20$
- Pin length: 14.80 ± 0.20
- Pin diameter: $5.45 \text{ TYP } [5.45 \pm 0.30]$
- Pin diameter: $0.75^{+0.20}_{-0.10}$
- Pin diameter: 2.00 ± 0.20
- Pin diameter: 2.00 ± 0.20
- Pin diameter: 2.00 ± 0.20
- Pin diameter: 4.00 ± 0.20
- Pin diameter: 2.50 ± 0.20

Side View Dimensions:

- Overall height: 22.00 ± 0.20
- Top section height: 5.50 ± 0.20
- Central slot width: 2.00 ± 0.20
- Pin diameter: $5.45 \text{ TYP } [5.45 \pm 0.30]$
- Pin diameter: $0.90^{+0.20}_{-0.10}$
- Pin diameter: 3.30 ± 0.20
- Pin diameter: 2.00 ± 0.20
- Pin diameter: 1.50 ± 0.20
- Pin diameter: 23.00 ± 0.20
- Pin diameter: 10.00 ± 0.20
- Pin diameter: 0.85 ± 0.03
- Pin diameter: 10°

Top View Dimensions:

- Overall width: 3.30 ± 0.20
- Overall height: 5.50 ± 0.20
- Central slot width: 2.00 ± 0.20

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result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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